International Workshop on SiP/SoC Integration of MEMS and Passive Components with RF-ICs

Tuesday, 2nd, March, 2004

Second International Symposium on Acoustic Wave Devices for Future Mobile Communication Systems

Wednesday, 3rd - Friday, 5th March, 2004

Keyaki Hall, Chiba University

Sponsored by

Japanese Ministry of Education, Culture, Sports, Science and Technology and Chiba University



Welcome to Chiba!

On behalf of Chiba University and the Organising Committee, I am most delighted to invite you to the Second International Symposium on Acoustic Wave Devices for Future Mobile Communication Systems, and International Workshop on SiP/SoC Integration of MEMS and Passive Components with RF-ICs.

The First Symposium, held right at the start of the 21st century, was an international meeting focussed upon the most important fields related to acoustic wave devices. Many researchers and engineers gathered at Chiba University from all over the world and discussed in detail how to respond to the rapidly changing needs of emerging communication technologies. This Symposium was a great success, with a total of 210 participants including 51 from overseas.

Now, over just the last three years, we have seen many novel developments in acoustic wave device technologies, as well as expanding users' demands for high bit rates and large capacities in mobile communications. For example, new devices



like FBARs and SMRs have already become competitive with conventional SAW and BAW devices, while IF filters have disappeared in some mobile phones. FBAR and SMR devices based on Si substrates are now expected to play a key role in realising SoC/SiP modules.

Therefore, the Organising Committee and Chiba University have again decided to offer researchers and engineers a platform to discuss future trends as well as state-of-the-art technologies related to acoustic wave device technologies and related field. The programme has been organised to cover a wide range of topics from materials to systems, with emphasis on (1) current status of, and future trends in, research and development related to acoustic wave devices, and (2) technical breakthroughs required for future mobile communication systems. I very much hope that you will be able to join us in helping to make this a most successful and fruitful opportunity for researchers and engineers working in these fields worldwide.

In conjunction with the Symposium, the workshop is newly organised to offer an opportunity to those involved in MEMS, passive-components and RF-ICs to discuss their ideas freely on future SiP/SoC integration of these devices. We hope the workshop will be a hot appetiser of the Symposium.

Finally, the organising committee is most indebted to the Japanese Ministry of Education, Culture, Sports, Science and Technology and the Chiba University for its sponsorship, and to NTT DoCoMo, Inc., Chiba Convention Bureau, Advantest Corp., Advanced Modular Sputtering Inc. with Matsubo Corp. and Unaxis Japan Co. Ltd. for their financial support.

2nd March, 2004

Masatsune Yamaguchi Chairman of the Organising Committee Professor of EEE Chiba University

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16:30

	A. Opening Remarks		
9:50	M. Yamaguchi, K. Hashimoto, Chiba University		
B. Impact of Passive Compo	onents in RF-ICs (Chair: K.Hashimoto, Chiba Univ.)		
10:10 Impact of RF-Integration			
•	H.Yoshida, Toshiba Corporate R&D Center		
10:40 Potential and Limitation of R	RF CMOS Technology and Expectation for New Passive		
Devices			
	A.Matsuzawa, Tokyo Institute of Technology		
11:10 Impact of Passive Devices in 1	RF Oscillators		
1	D.Ham, Harvard University		
C. Integration of Acous	tic Wave Devices (Chair: T.Omori, Chiba Univ.)		
·	Technologies for Oscillator Applications		
	C.S.Lam, TXC Corp.		
13:20 Integration Aspects of FBAR	, · · · · · · · · · · · · · · · · · · ·		
	R.Aigner, Infineon Technologies AG		
13:50 Integration of SAW (BAW) D			
,	C.Ruppel, P.Hagn, P.Heide and S.Seitz, EPCOS AG		
D. RF-MEMS and Micro-A	Assembly (Chair: P.Z.Chang, National Taiwan Univ.)		
14:40 A Capacitive RF MEMS Shur	nt Switch		
•	S.Kobayashi, H.Kawai, Murata MFG, Co. Ltd.		
15:10 Stability Issues in MEMS Dev			
·	H.Toshiyoshi, University of Tokyo		
15:40 Fujitsu's Highly Integrated			
• 5 •	M.Natsuaki, Fujitsu Ltd.		
E Panal Disaussian (Ma	adamatan D. Waigal Univ. Eulangan Nurambang)		

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Opening Remarks

M. Yamaguchi, Chiba University

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